

HSK277

Silicon Epitaxial Planar Diode for UHF/VHF tuner Band Switch

HITACHI

Rev. 1
Jun. 1994

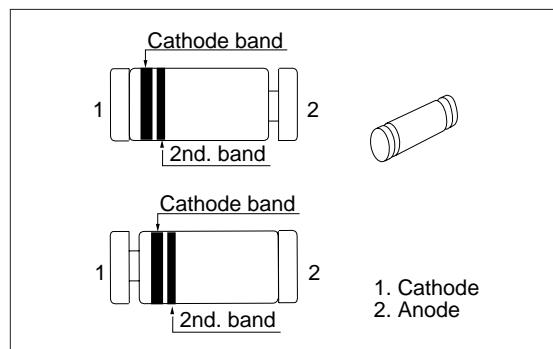
Features

- Low forward resistance. ($r_f = 0.5\Omega$ max)
- LLD package is suitable for high density surface mounting and high speed assembly.

Ordering Information

| Type No. | Cathode Band | 2nd Band | Package code |
|----------|--------------|----------|--------------|
| HSK277 | Verdure | Blue | LLD |

Outline



Absolute Maximum Ratings ($T_a = 25^\circ C$)

| Item | Symbol | Value | Unit |
|-----------------------|-----------|-------------|------|
| Reverse voltage | V_R | 35 | V |
| Forward current | I_F | 100 | mA |
| Power dissipation | P_d | 150 | mW |
| Operation temperature | T_{opr} | -20 to + 60 | °C |
| Storage temperature | T_{stg} | -55 to +150 | °C |

Electrical Characteristics ($T_a = 25^\circ C$)

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|--------------------|--------|-----|-----|-----|------|---|
| Forward voltage | V_F | — | — | 1.0 | V | $I_F = 10 \text{ mA}$ |
| Reverse voltage | V_R | 35 | — | — | V | $I_R = 10 \mu\text{A}$ |
| Reverse current | I_R | — | — | 10 | nA | $V_R = 25 \text{ V}$ |
| Capacitance | C | — | — | 1.2 | pF | $V_R = 6 \text{ V}, f = 1 \text{ MHz}$ |
| Forward resistance | r_f | — | — | 0.5 | Ω | $I_F = 2 \text{ mA}, f = 100 \text{ MHz}$ |

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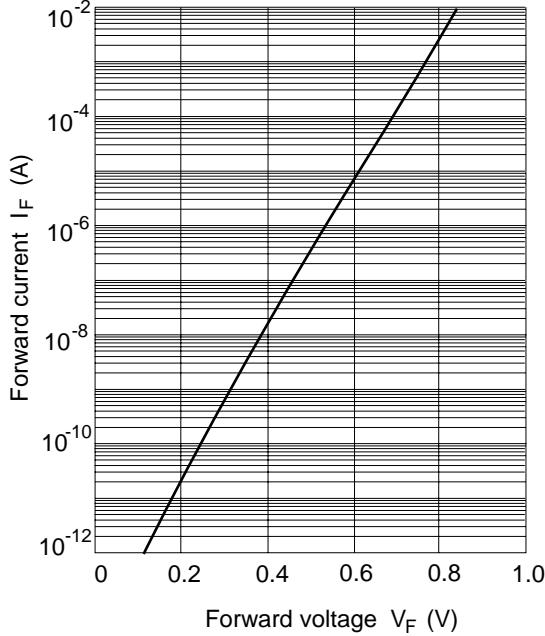


Fig.1 Forward current Vs.
Forward voltage

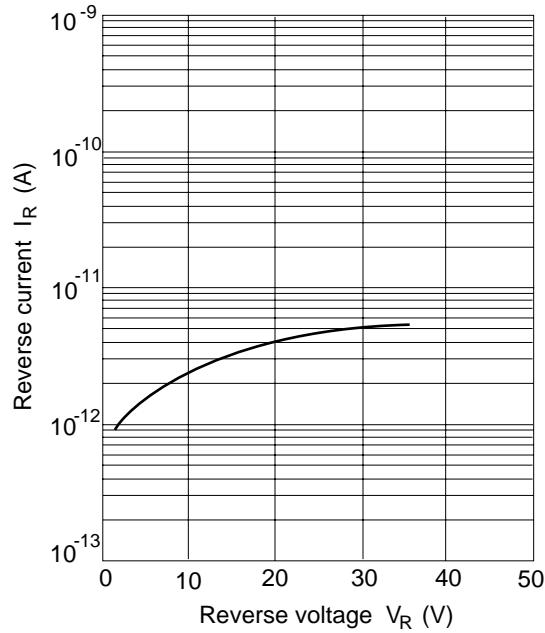


Fig.2 Reverse current Vs.
Reverse voltage

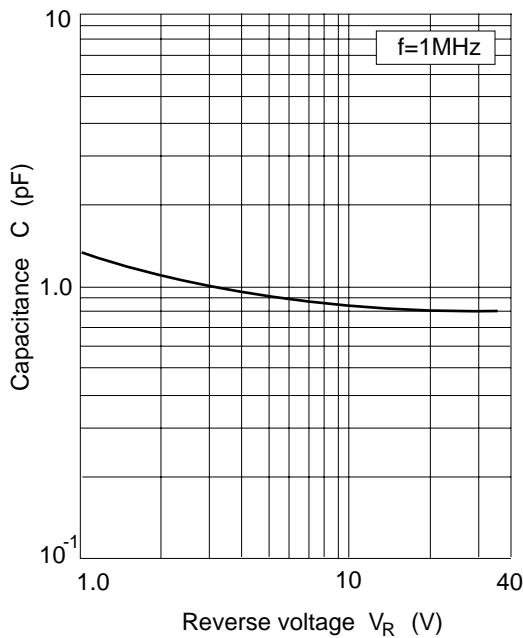


Fig.3 Capacitance Vs.
Reverse voltage

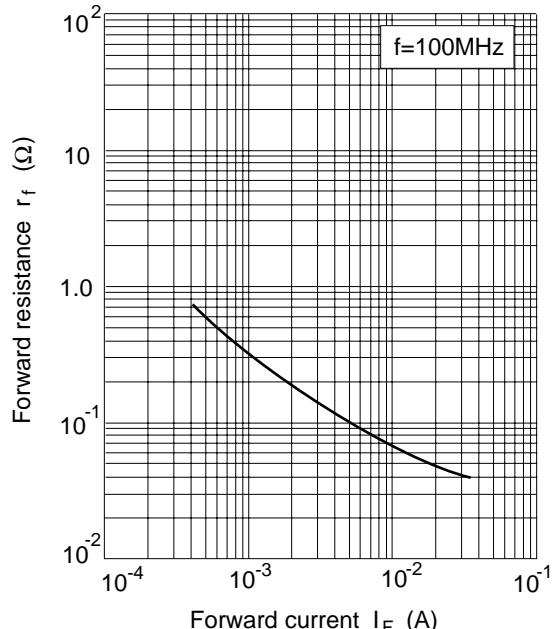
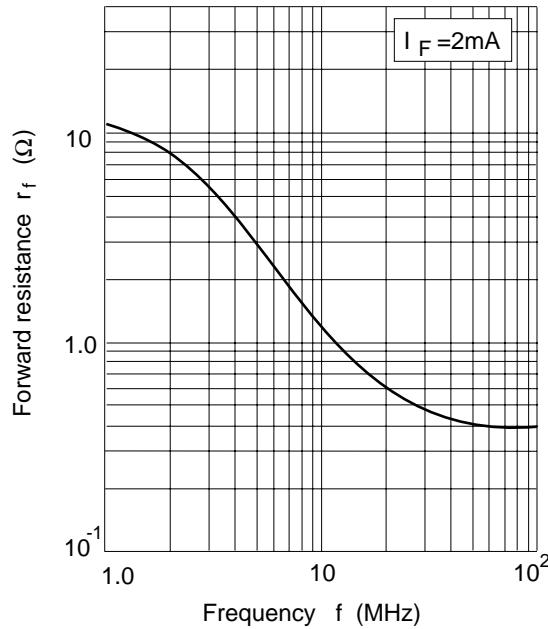


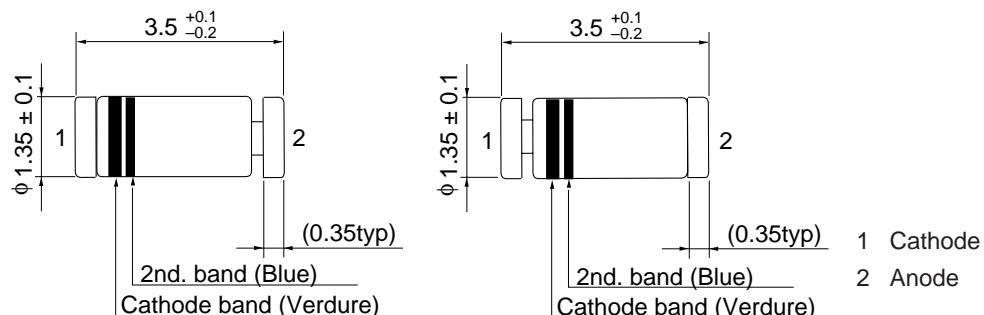
Fig.4 Forward resistance
Vs. Forward current



**Fig.5 Forward resistance
Vs. Frequency**

Package Dimensions

Unit: mm



() : Reference only

| | |
|--------------|-------|
| HITACHI Code | LLD |
| JEDEC Code | — |
| EIAJ Code | — |
| Weight (g) | 0.027 |